# **Quad 2-Input AND Gate**

## **High-Performance Silicon-Gate CMOS**

#### **Features**

- Outputs Source/Sink 24 mA
- 'ACT08 Has TTL Compatible Inputs
- These are Pb–Free Devices

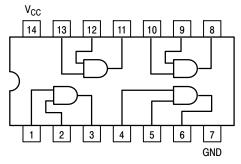


Figure 1. Pinout: 14-Lead Packages Conductors (Top View)



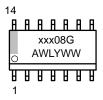
### ON Semiconductor®

#### www.onsemi.com

#### MARKING DIAGRAMS

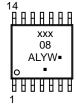


SOIC-14 D SUFFIX CASE 751A





TSSOP-14 DT SUFFIX CASE 948G



xxx = AC or ACT

A = Assembly Location

WL or L = Wafer Lot Y = Year WW or W = Work Week G or = Pb-Free Package

(Note: Microdot may be in either location)

#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

#### **MAXIMUM RATINGS**

Symbol	Paramet	ter	Value	Unit
V <sub>CC</sub>	DC Supply Voltage		-0.5  to  +7.0	V
VI	DC Input Voltage		$-0.5 \le V_I \le V_{CC} + 0.5$	V
Vo	DC Output Voltage	(Note 1)	$-0.5 \le V_{O} \le V_{CC} + 0.5$	V
I <sub>IK</sub>	DC Input Diode Current		±20	mA
lok	DC Output Diode Current		±50	mA
Io	DC Output Sink/Source Current		±50	mA
Icc	DC Supply Current per Output Pin		±50	mA
I <sub>GND</sub>	DC Ground Current per Output Pin		±50	mA
T <sub>STG</sub>	Storage Temperature Range		-65 to +150	°C
TL	Lead temperature, 1 mm from Case fo	r 10 Seconds	260	°C
TJ	Junction temperature under Bias		+ 150	°C
$\theta_{JA}$	Thermal Resistance (Note 2)	SOIC TSSOP	125 170	°C/W
P <sub>D</sub>	Power Dissipation in Still Air at 85°C	SOIC TSSOP	125 170	mW
MSL	Moisture Sensitivity		Level 1	
F <sub>R</sub>	Flammability Rating	Oxygen Index: 30% – 35%	UL 94 V-0 @ 0.125 in	
V <sub>ESD</sub>	ESD Withstand Voltage	Human Body Model (Note 3) Machine Model (Note 4) Charged Device Model (Note 5)	> 2000 > 200 > 1000	V
I <sub>Latch-Up</sub>	Latch-Up Performance Above V <sub>CC</sub> a	and Below GND at 85°C (Note 6)	±100	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. Io absolute maximum rating must be observed.
- The package thermal impedance is calculated in accordance with JESD51–7.
   Tested to EIA/JESD22–A114–A.
- 4. Tested to EIA/JESD22-A115-A.
- 5. Tested to JESD22-C101-A.
- 6. Tested to EIA/JESD78.

### RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Тур	Max	Unit
	0 1 1 1 1	'AC	2.0	5.0	6.0	.,
$V_{CC}$	/cc Supply Voltage		4.5	5.0	5.5	V
V <sub>in</sub> , V <sub>out</sub>	DC Input Voltage, Output Voltage (Ref. to GND)		0	_	V <sub>CC</sub>	V
		V <sub>CC</sub> @ 3.0 V	_	150	-	ns/V
t <sub>r</sub> , t <sub>f</sub>	Input Rise and Fall Time (Note 1)  'AC Devices except Schmitt Inputs	V <sub>CC</sub> @ 4.5 V	_	40	-	
	Ac Devices except definite inputs	V <sub>CC</sub> @ 5.5 V	ı	25	-	
	Input Rise and Fall Time (Note 2)	V <sub>CC</sub> @ 4.5 V	ı	10	-	A /
t <sub>r</sub> , t <sub>f</sub>	'ACT Devices except Schmitt Inputs	V <sub>CC</sub> @ 5.5 V	ı	8.0	-	ns/V
TJ	Junction Temperature (PDIP)		ı	_	140	°C
T <sub>A</sub>	Operating Ambient Temperature Range		-40	25	85	°C
I <sub>OH</sub>	Output Current – High		-	_	-24	mA
I <sub>OL</sub>	Output Current – Low		-	-	24	mA

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

- V<sub>in</sub> from 30% to 70% V<sub>CC</sub>; see individual Data Sheets for devices that differ from the typical input rise and fall times.
   V<sub>in</sub> from 0.8 V to 2.0 V; see individual Data Sheets for devices that differ from the typical input rise and fall times.

#### **DC CHARACTERISTICS**

					74.	AC	74AC	
				V <sub>CC</sub>	T <sub>A</sub> = -	+25°C	T <sub>A</sub> = -40°C to +85°C	
Symbol	Parameter	Con	ditions	(V)	Тур	Guar	anteed Limits	Unit
V <sub>IH</sub>	Minimum High Level Input Voltage	V <sub>OUT</sub> = 0.1 V or V <sub>CC</sub> - 0.1 V	,	3.0 4.5 5.5	1.5 2.25 2.75	2.1 3.15 3.85	2.1 3.15 3.85	V
V <sub>IL</sub>	Maximum Low Level Input Voltage	V <sub>OUT</sub> = 0.1 V or V <sub>CC</sub> – 0.1 V	,	3.0 4.5 5.5	1.5 2.25 2.75	0.9 1.35 1.65	0.9 1.35 1.65	V
V <sub>OH</sub>	Minimum High Level Output Voltage	I <sub>OUT</sub> = -50 μA		3.0 4.5 5.5	2.99 4.49 5.49	2.9 4.4 5.4	2.9 4.4 5.4	V
		$V_{IN} = V_{IL}$ or $V_{I}$	H (Note 3) -12 mA -24 mA -24 mA	3.0 4.5 5.5	- - -	2.56 3.86 4.86	2.46 3.76 4.76	V
V <sub>OL</sub>	Maximum Low Level Output Voltage	$V_{IN} = V_{IL} \text{ or } V_{I}$ $I_{OL}$	H(Note 3) 12 mA 24 mA 24 mA	3.0 4.5 5.5	- - -	0.36 0.36 0.36	0.44 0.44 0.44	V
I <sub>IN</sub>	Maximum Input Leakage Current	$V_I = V_{CC}$ , GNI	)	5.5	-	±0.1	±1.0	μΑ
I <sub>OLD</sub>	Minimum Dynamic (Note 4)	V <sub>OLD</sub> = 1.65 V	Max	5.5	-	_	75	mA
I <sub>OHD</sub>	Output Current	V <sub>OHD</sub> = 3.85 \	' Min	5.5	-	-	-75	mA
Icc	Maximum Quiescent Supply Current	$V_{IN} = V_{CC}$ or $C$	GND	5.5	-	4.0	40	μΑ

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

NOTE:  $I_{IN}$  and  $I_{CC}$  @ 3.0 V are guaranteed to be less than or equal to the respective limit @ 5.5 V  $V_{CC}$ .

- 3. All outputs loaded; thresholds on input associated with output under test.
- 4. Maximum test duration 2.0 ms, one output loaded at a time.

### **AC CHARACTERISTICS**

				74AC		74.	AC		
		V <sub>CC</sub> (V)		գ = +25° ել = 50 p		T <sub>A</sub> = - to +8 C <sub>L</sub> = 9	85°C		Fig.
Symbol	Parameter	(Note5)	Min	Тур	Max	Min	Max	Unit	No.
t <sub>PLH</sub>	Propagation Delay	3.3 5.0	1.5 1.5	7.5 5.5	9.5 7.5	1.0 1.0	10.0 8.5	ns	3–5
t <sub>PHL</sub>	Propagation Delay	3.3 5.0	1.5 1.5	7.0 5.5	8.5 7.0	1.0 1.0	9.0 7.5	ns	3–5

<sup>5.</sup> Voltage Range 3.3 V is 3.3 V  $\pm 0.3$  V. Voltage Range 5.0 V is 5.0 V  $\pm 0.5$  V.

### **DC CHARACTERISTICS**

					74	CT	74ACT	
				V <sub>cc</sub>	T <sub>A</sub> =	+25°C	T <sub>A</sub> = -40°C to +85°C	
Symbol	Parameter	Condition	ons	(V)	Тур	Guar	anteed Limits	Unit
V <sub>IH</sub>	Minimum High Level	V <sub>OUT</sub> = 0.1 V		4.5	1.5	2.0	2.0	V
	Input Voltage	or V <sub>CC</sub> – 0.1 V		5.5	1.5	2.0	2.0	V
V <sub>IL</sub>	Maximum Low Level	V <sub>OUT</sub> = 0.1 V		4.5	1.5	0.8	0.8	V
	Input Voltage	or V <sub>CC</sub> – 0.1 V		5.5	1.5	0.8	0.8	V
V <sub>OH</sub>	Minimum High Level	I <sub>OUT</sub> = -50 μA		4.5	4.49	4.4	4.4	V
	Output Voltage			5.5	5.49	5.4	5.4	V
		$V_{IN} = V_{IL}$ or $V_{IH}$ (N	lote 6)					V
			–24 mA	4.5	_	3.86	3.76	
			–24 mA	5.5	_	4.86	4.76	
V <sub>OL</sub>	Maximum Low Level	I <sub>OUT</sub> = 50 μA		4.5	0.001	0.1	0.1	V
	Output Voltage			5.5	0.001	0.1	0.1	V
		$V_{IN} = V_{IL} \text{ or } V_{IH} \text{ (N)}$	lote 6)					V
			24 mA	4.5	_	0.36	0.44	
			24 mA	5.5	_	0.36	0.44	
I <sub>IN</sub>	Maximum Input Leakage Current	$V_I = V_{CC}$ , GND		5.5	-	±0.1	±1.0	μΑ
$\Delta I_{CCT}$	Additional Max. I <sub>CC</sub> /Input	$V_{I} = V_{CC} - 2.1 \text{ V}$		5.5	0.6	-	1.5	mA
I <sub>OLD</sub>	Minimum Dynamic (Note 7)	V <sub>OLD</sub> = 1.65 V Ma	х	5.5	_	-	75	mA
I <sub>OHD</sub>	Output Current	V <sub>OHD</sub> = 3.85 V Min	า	5.5	_	-	<b>-</b> 75	mA
I <sub>CC</sub>	Maximum Quiescent Supply Current	V <sub>IN</sub> = V <sub>CC</sub> or GND	1	5.5	-	4.0	40	μΑ

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

6. All outputs loaded; thresholds on input associated with output under test.

7. Maximum test duration 2.0 ms, one output loaded at a time.

#### **AC CHARACTERISTICS**

				74ACT		74A	СТ		
			_		•	T <sub>A</sub> = -			
				<sub>4</sub> = +25° <sub>L</sub> = 50 p		to +8			
Symbol	Parameter	V <sub>CC</sub> (V) (Note 8)	Min	Тур	Max	Min	Max	Unit	Fig. No.
t <sub>PLH</sub>	Propagation Delay	5.0	1.0	-	9.0	1.0	10.0	ns	3–5
t <sub>PHL</sub>	Propagation Delay	5.0	1.0	-	9.0	1.0	10.0	ns	3–5

<sup>8.</sup> Voltage Range 5.0 V is 5.0 V  $\pm 0.5$  V.

#### **CAPACITANCE**

Symbol	Parameter	Test Conditions	Value Typ	Unit
C <sub>IN</sub>	Input Capacitance	V <sub>CC</sub> = 5.0 V	4.5	pF
C <sub>PD</sub>	Power Dissipation Capacitance	V <sub>CC</sub> = 5.0 V	20	pF

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MC74AC08DG	SOIC-14 (Pb-Free)	55 Units / Rail
MC74AC08DR2G	SOIC-14 (Pb-Free)	2500 / Tape & Reel
MC74AC08DTR2G	TSSOP-14 (Pb-Free)	2500 / Tape & Reel
MC74ACT08DG	SOIC-14 (Pb-Free)	55 Units / Rail
MC74ACT08DR2G	SOIC-14 (Pb-Free)	2500 / Tape & Reel
MC74ACT08DTR2G	TSSOP-14 (Pb-Free)	2500 / Tape & Reel

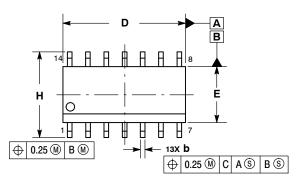
<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

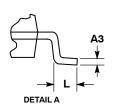


0.10

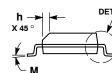
SOIC-14 NB CASE 751A-03 ISSUE L

**DATE 03 FEB 2016** 









- NOTES:
  1. DIMENSIONING AND TOLERANCING PER
  - ASME Y14.5M, 1994.
    CONTROLLING DIMENSION: MILLIMETERS.
  - DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF AT
- MAXIMUM MATERIAL CONDITION.
  DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSIONS.
- 5. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE

	MILLIMETERS INCHE			HES
DIM	MIN MAX		MIN	MAX
Α	1.35	1.75	0.054	0.068
A1	0.10	0.25	0.004	0.010
АЗ	0.19	0.25	0.008	0.010
b	0.35	0.49	0.014	0.019
D	8.55	8.75	0.337	0.344
Е	3.80	4.00	0.150	0.157
е	1.27	BSC	0.050	BSC
Н	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.019
L	0.40	1.25	0.016	0.049
M	0 °	7°	0 °	7°

#### **GENERIC MARKING DIAGRAM\***



XXXXX = Specific Device Code Α = Assembly Location

WL = Wafer Lot Υ = Year WW = Work Week = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator. "G" or microdot " ■". may or may not be present.

## **SOLDERING FOOTPRINT\***

1	6.50 –	<b>-</b>	14X 1.18
			_ 1.27
_			PITCH
14X 1			_
14X 10.58			

**DIMENSIONS: MILLIMETERS** 

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### **STYLES ON PAGE 2**

DOCUMENT NUMBER:	98ASB42565B	Electronic versions are uncontrolled except when accessed directly from Printed versions are uncontrolled except when stamped "CONTROLLED"	
DESCRIPTION:	SOIC-14 NB		PAGE 1 OF 2

ON Semiconductor and (III) are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

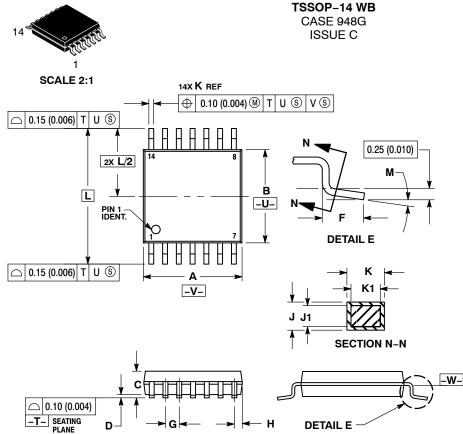
#### SOIC-14 CASE 751A-03 ISSUE L

### DATE 03 FEB 2016

STYLE 1: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. NO CONNECTION 5. ANODE/CATHODE 6. NO CONNECTION 7. ANODE/CATHODE 8. ANODE/CATHODE 9. ANODE/CATHODE 10. NO CONNECTION 11. ANODE/CATHODE 12. ANODE/CATHODE 13. NO CONNECTION 14. COMMON ANODE	STYLE 2: CANCELLED	STYLE 3: PIN 1. NO CONNECTION 2. ANODE 3. ANODE 4. NO CONNECTION 5. ANODE 6. NO CONNECTION 7. ANODE 8. ANODE 9. ANODE 10. NO CONNECTION 11. ANODE 12. ANODE 13. NO CONNECTION 14. COMMON CATHODE	STYLE 4: PIN 1. NO CONNECTION 2. CATHODE 3. CATHODE 4. NO CONNECTION 5. CATHODE 6. NO CONNECTION 7. CATHODE 8. CATHODE 9. CATHODE 10. NO CONNECTION 11. CATHODE 12. CATHODE 13. NO CONNECTION 14. COMMON ANODE
STYLE 5: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. ANODE/CATHODE 5. ANODE/CATHODE 6. NO CONNECTION 7. COMMON ANODE 8. COMMON CATHODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. ANODE/CATHODE 12. ANODE/CATHODE 12. ANODE/CATHODE 13. NO CONNECTION 14. COMMON ANODE	STYLE 6: PIN 1. CATHODE 2. CATHODE 3. CATHODE 4. CATHODE 5. CATHODE 6. CATHODE 7. CATHODE 8. ANODE 9. ANODE 10. ANODE 11. ANODE 12. ANODE 13. ANODE 14. ANODE	STYLE 7: PIN 1. ANODE/CATHODE 2. COMMON ANODE 3. COMMON CATHODE 4. ANODE/CATHODE 5. ANODE/CATHODE 6. ANODE/CATHODE 7. ANODE/CATHODE 8. ANODE/CATHODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. COMMON CATHODE 12. COMMON ANODE 13. ANODE/CATHODE 14. ANODE/CATHODE	STYLE 8: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. NO CONNECTION 5. ANODE/CATHODE 6. ANODE/CATHODE 7. COMMON ANODE 8. COMMON ANODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. NO CONNECTION 12. ANODE/CATHODE 13. ANODE/CATHODE 14. COMMON CATHODE

DOCUMENT NUMBER:	98ASB42565B	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	SOIC-14 NB		PAGE 2 OF 2

ON Semiconductor and IN are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.



**DATE 17 FEB 2016** 

- NOTES.

  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

  2. CONTROLLING DIMENSION: MILLIMETER.

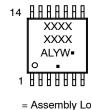
  3. DIMENSION A DOES NOT INCLUDE MOLD
- FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
  DIMENSION B DOES NOT INCLUDE
- INTERLEAD FLASH OR PROTRUSION.
  INTERLEAD FLASH OR PROTRUSION SHALL
- INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.

  5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.

  6. TERMINAL NUMBERS ARE SHOWN FOR DEFERENCE ONLY.
- REFERENCE ONLY.
  DIMENSION A AND B ARE TO BE
  DETERMINED AT DATUM PLANE -W-.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
Н	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
М	0°	8 °	0 °	8 °

#### **GENERIC MARKING DIAGRAM\***



= Assembly Location

= Wafer Lot ٧ = Year

W = Work Week

= Pb-Free Package (Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

SOLDERING FOOTPRINT				
7.	06			
1				
<del></del>				
J	————   PITCH			
14X 0.36	<del></del>			
0.36 → 1.26	DIMENSIONS: MILLIMETERS			

DOCUMENT NUMBER:	98ASH70246A	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	TSSOP-14 WB		PAGE 1 OF 1	

ON Semiconductor and unare trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

ON Semiconductor and the are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at <a href="www.onsemi.com/site/pdf/Patent-Marking.pdf">www.onsemi.com/site/pdf/Patent-Marking.pdf</a>. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor and see no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and

#### **PUBLICATION ORDERING INFORMATION**

LITERATURE FULFILLMENT:
Email Requests to: orderlit@onsemi.com

ON Semiconductor Website: www.onsemi.com

TECHNICAL SUPPORT
North American Technical Support:
Voice Mail: 1 800-282-9855 Toll Free USA/Canada

Europe, Middle East and Africa Technical Support: a Phone: 00421 33 790 2910

Phone: 011 421 33 790 2910 For additional information, please contact your local Sales Representative